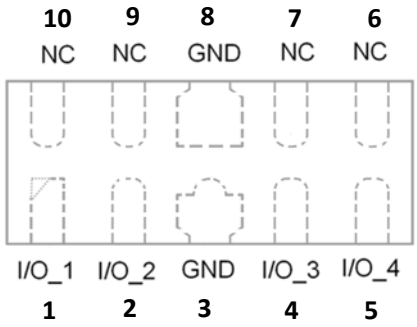
AZ1213-04F

4-Line Ultra Low Capacitance TVS Diode Array

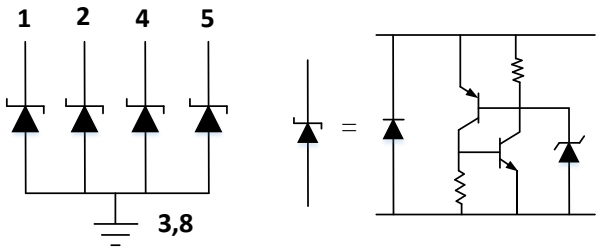
Features

- Ultra low capacitance: 0.25pF typical (I/O to I/O)
- Ultra low leakage: nA level
- Working voltage: 3.3V- 5V
- Low clamping voltage
- Up to 4 lines protects
- Leadless flow-through package
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test
    - Air discharge: ±30kV
    - Contact discharge: ±30kV
  - IEC61000-4-5 (Lightning) 14A (8/20μs)
- RoHS Compliant

Dimensions DFN2510P10



Pin Configuration



Applications

- USB & HDMI Interfaces
- Portable electronics
- Servers, notebooks, and desktop PCs
- Set-top box
- Communication systems
- PoE

Mechanical Characteristics

- Package: DFN2510-10
- Lead Finish: Matte Tin
- Case Material: “Green” Molding Compound.
- Quantity Per Reel:3,000 pcs
- Reel Size:7 inch
- Device Marking: .3V4UC

Absolute Maximum Ratings (Tamb=25°C unless otherwise specified)

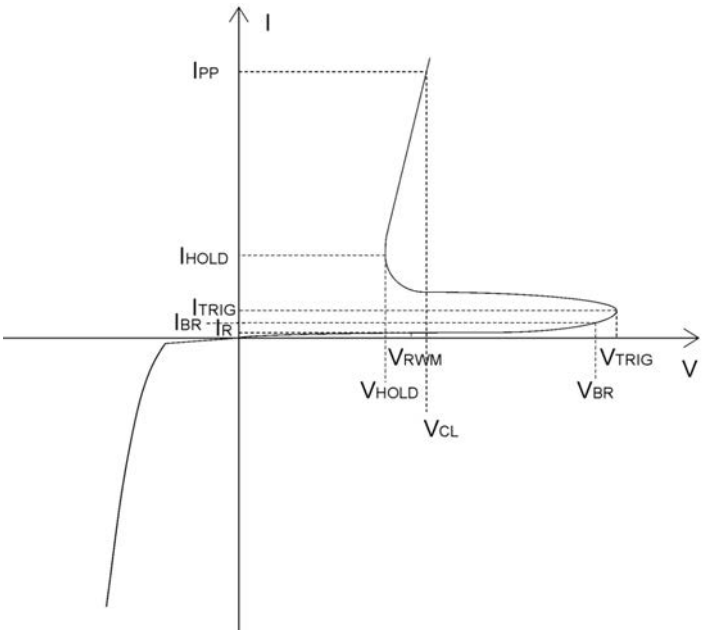
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppp	100	W
ESD per IEC 61000−4−2 (Air)	V_{ESD}	± 30	kV
ESD per IEC 61000−4−2 (Contact)		± 30	
Operating Temperature Range	T_J	-40 to +125	℃
Storage Temperature Range	T_{STJ}	-55 to +150	℃

Electrical Characteristics(TA=25°C unless otherwise specified)

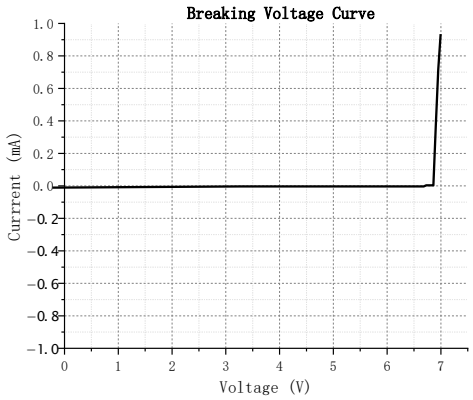
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Reverse Stand-off Voltage	V_{RWM}			3.3	5.0	V
Reverse Breakdown Voltage	V_{BR}	IT=1mA	5.5	7.1	8.5	V
Reverse Leakage Current	I_R	V_{RWM}=3.3V		1.0	100	nA
Clamping Voltage	V_{CL}	I_{PP}=1A; tp=8/20us		1.5	2.5	V
Clamping Voltage	V_{CL}	I_{PP}=14A; tp=8/20us		5.6	7.0	V
Junction Capacitance	C_J	VR=1.65V; f=1MHz；IO-GND		0.45	0.55	pF
		VR=1.65V; f=1MHz；IO-IO		0.25	0.35	

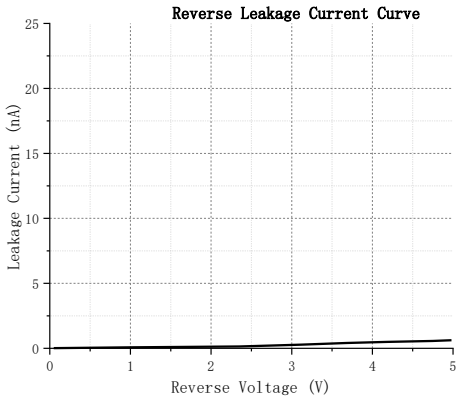
Electrical Parameters(TA=25°C unless otherwise specified)

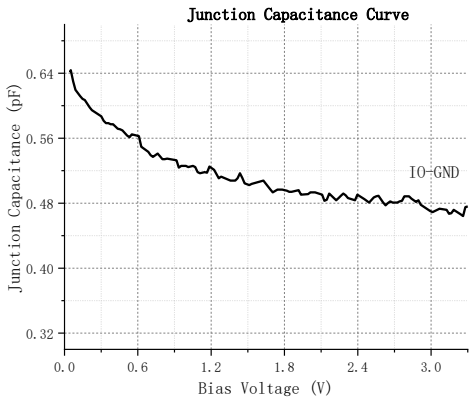
Symbol	Parameters
V_{RWM}	Reverse stand-off voltage
I_R	Reverse leakage current
V_{BR}	Reverse breakdown voltage
I_{BR}	Reverse breakdown current
V_{CL}	Clamping voltage
V_{TRIG}	Reverse trigger voltage
I_{TRIG}	Reverse trigger current
V_{HOLD}	Reverse holding voltage
I_{HOLD}	Reverse holding current
I_{PP}	Peak pulse current

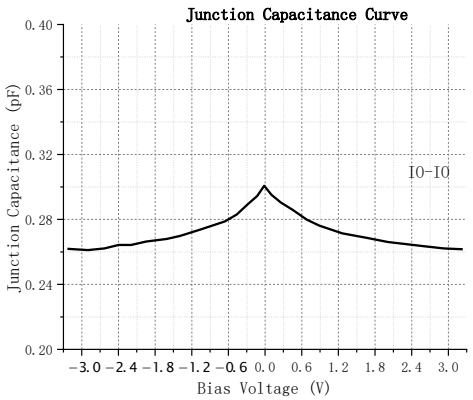


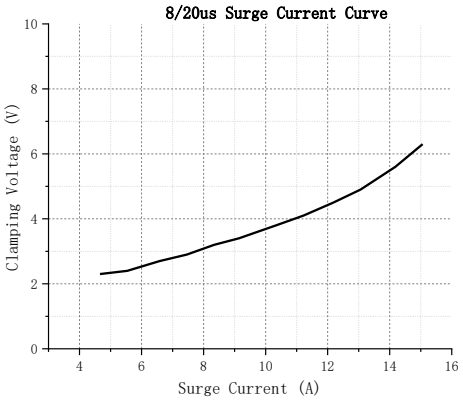
Typical Performance Characteristics(TA=25°C unless otherwise specified)

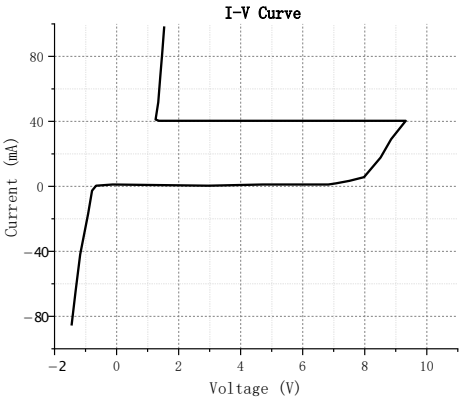




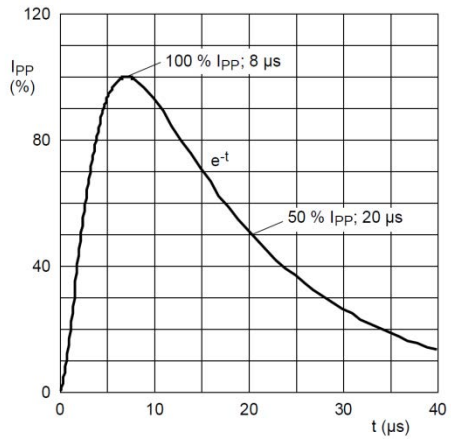




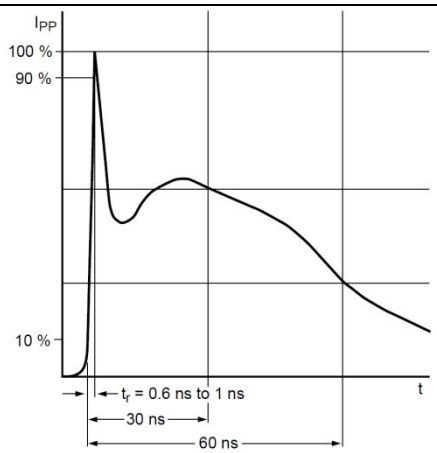




Measurement Wave According to IEC Standard

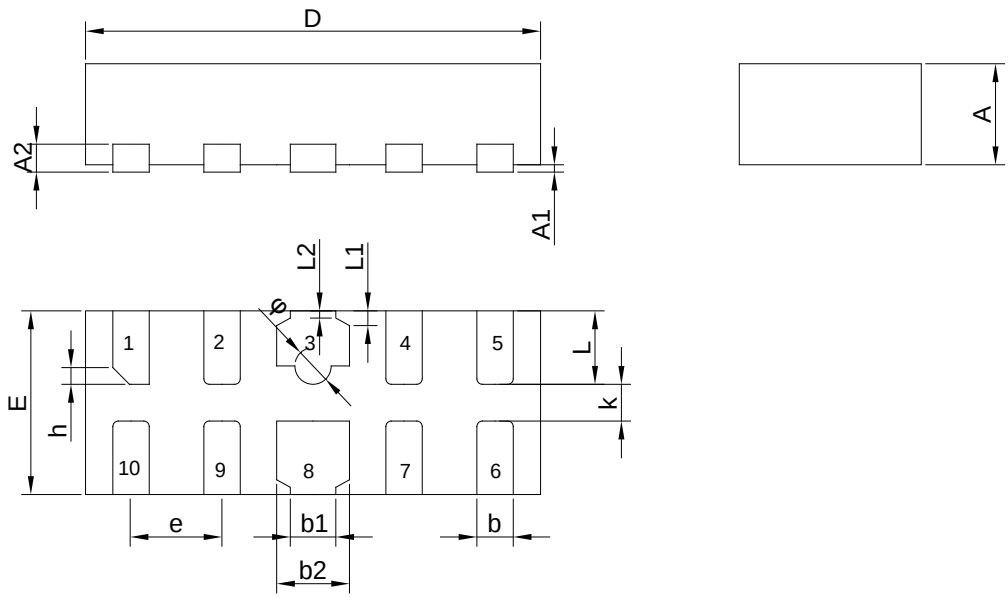


8/20 µs pulse waveform according to IEC 61000-4-5



ESD pulse waveform according to IEC 61000-4-2

DFN2510-10 Package Outline Drawing



Dimensions in Millimeter							
Symbol	Min.	Nom.	Max.	Symbol	Min.	Nom.	Max.
A	0.500	0.550	0.600	D	2.450	2.500	2.550
A1	0.00	/	0.05	E	0.950	1.00	1.050
A2	0.122	0.152	0.200	e	0.450	0.500	0.550
b	0.150	0.200	0.250	h	0.080	0.120	0.150
b1	0.200	0.250	0.300	k	0.150	0.200	0.250
b2	0.350	0.400	0.450	L	0.350	0.400	0.450
L1	0.075 REF			L2	0.05 REF		
φ	0.150	0.200	0.250				

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